PATENT

H / Election

G/24/02

Admit

Jurgen Vollrath

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

| In re application of | |) | A + T I : + | | | |
|-----------------------|----------------------|---|---------------------|-------|--------------|------------|
| Inventor: | Vladislav Vashchenko |) | Art Unit: 2811 | | | |
| Serial No.: | 09/944,426 |) | | TECHN | | |
| Filed: | August 30, 2001 |) | Examiner: Ori Nadav | | 47.5 47.5 | .70 [1] |
| Title: | HIGH HOLDING VOLTAGE |) | | | P 20 | CE |
| LVTSCR-LIKE STRUCTURE | |) | | | 2002 | |
| Commissione | r for Patents | | • | 2800 | | |

RESPONSE TO RESTRICTION/ELECTION REQUIREMENT AND CORRECTION

Election:

Washington, D.C. 20231

The examiner is thanked for his Office action mailed 8/12/2002, which has been studied in detail.

Applicant elects Group II, Claims 2-8, drawn to a process of making a semiconductor device.

Correction:

Please correct the first line of the Field of the Invention section (page 1) as follows:

Replace "relyy7ates" with -- relates --.

Page 6, line 21:

Replace "w=25m, 50m, 100m, respectively." with -- w=25μm, 50μm, 100μm, respectively.--

Page 6, line 31:

Replace "compacitance" with -- capacitance --.

